Claims

1. A semiconductor device comprising:

a stacked body including a first electrode layer, a second electrode layer, and a third electrode layer, the second electrode layer provided to be electrically insulated from the first electrode layer in a stacking direction, the third electrode layer interposed between the second electrode layer and the first electrode layer in the stacking direction and provided to be electrically insulated;

at least two first insulating layers provided in the stacked body to range from an upper end of the stacked body to a lower end of the stacked body, and extending in a first direction intersecting the stacking direction;

a first staircase portion provided in a first end region of the stacked body between the at least two first insulating layers;

a second staircase portion provided in a second end region of the stacked body located on a side opposite to the first end region between the at least two first insulating layers;

a second insulating layer extending in the first direction, the second insulating layer provided in the stacked body between the at least two first insulating layers, and dividing the second electrode layer and the third electrode layer in a second direction crossing the first direction; and

an interconnection electrically connecting the first electrode layer and the third electrode layer in the stacked body, wherein

the first electrode layer is a first word line,

the second electrode layer is a selection gate layer, and

the third electrode layer is a second word line.

2. The device according to claim 1, wherein

the first word line is a first dummy word line, and

the second word line is a second dummy word line.

3. The device according to claim 1, wherein

the stacked body includes a first column-shaped portion provided in an intermediate region of the stacked body located between the first end region and the second end region, the first column-shaped portion extending in the stacking direction, and

the first column-shaped portion includes:

a semiconductor body extending in the stacking direction; and

a charge storage portion provided between the semiconductor body and the first electrode layer.

4. The device according to claim 1, wherein

the interconnection is provided outside the stacked body, and

the interconnection is provided above at least one of the first end region and the second end region.

5. The device according to claim 1, wherein

the interconnection is provided in the stacked body, and

the interconnection is provided below the second insulating layer.

6. The device according to claim 3, wherein

the stacked body includes a second column-shaped portion penetrating the second insulating layer and extending in the stacking direction,

the second column-shaped portion has the same structure as the first column-shaped portion, and

the interconnection is provided along the second column-

shaped portion.